BLF6G20-110; BLF6G20LS-110

Power LDMOS transistor

Rev. 03 — 13 January 2009 Product data sheet

1. Product profile

1.1 General description

110 W LDMOS power transistor for base station applications at frequencies from 1800 MHz to 2000 MHz.

Table 1. Typical performance

RF performance at T_{case} = 25 °C in a common source class-AB production test circuit.

Mode of operation	f	V_{DS}	$P_{L(AV)}$	G_p	η_D	IMD3	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)	(dBc)
2-carrier W-CDMA	1930 to 1990	28	25	19	32	–34[1]	–38[1]

[1] Test signal: 3GPP; test model 1; 64 DPCH; PAR = 7 dB at 0.01 % probability on CCDF per carrier; carrier spacing 10 MHz.

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

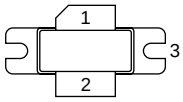
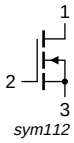
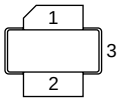
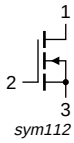
- Typical 2-carrier W-CDMA performance at frequencies of 1930 MHz and 1990 MHz, a supply voltage of 28 V and an I_{Dq} of 900 mA:
  - Average output power = 25 W
  - Power gain = 19 dB
  - Efficiency = 32 %
  - IMD3 = –34 dBc
  - ACPR = –38 dBc
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (1800 MHz to 2000 MHz)
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- RF power amplifiers for GSM, GSM EDGE, W-CDMA and CDMA base stations and multicarrier applications in the 1800 MHz to 2000 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
BLF6G20-110 (SOT502A)				
1	drain			 sym112
2	gate			
3	source	[1]		
BLF6G20LS-110 (SOT502B)				
1	drain			 sym112
2	gate			
3	source	[1]		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF6G20-110	-	flanged LDMOST ceramic package; 2 mounting holes; 2 leads	SOT502A
BLF6G20LS-110	-	earless flanged LDMOST ceramic package; 2 leads	SOT502B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		–0.5	+13	V
I_D	drain current		-	29	A
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		-	225	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Type	Typ	Unit
$R_{th(j-case)}$	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 25 W (CW)	BLF6G20-110	0.52	K/W
			BLF6G20LS-110	0.45	K/W

6. Characteristics

Table 6. Characteristics

T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.5 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 150 mA	1.4	2	2.4	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_D = 950 mA	1.6	2.1	2.6	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	5	µA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	22.3	27	-	A
I_{GSS}	gate leakage current	V_{GS} = 13 V; V_{DS} = 0 V	-	-	450	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 7.5 A	-	10.5	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 5.25 A	-	0.1	0.160	Ω
C_{rs}	feedback capacitance	V_{GS} = 0 V; V_{DS} = 28 V; f = 1 MHz	-	2.1	-	pF

7. Application information

Table 7. Application information

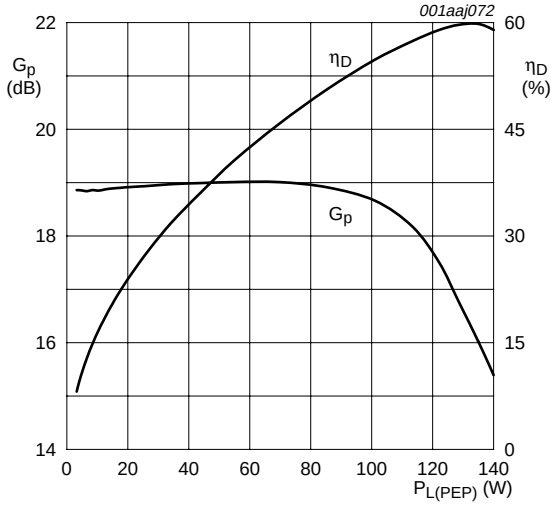
Mode of operation: 2-carrier W-CDMA; PAR 7 dB at 0.01 % probability on CCDF; 3GPP test model 1; 1-64 PDPCH; f_1 = 1932.5 MHz; f_2 = 1942.5 MHz; f_3 = 1977.5 MHz; f_4 = 1987.5 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 900 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$P_{L(AV)}$	average output power		-	25	-	W
G_p	power gain	$P_{L(AV)}$ = 25 W	18	19	-	dB
η_D	drain efficiency	$P_{L(AV)}$ = 25 W	28	32	-	%
IMD3	third order intermodulation distortion	$P_{L(AV)}$ = 25 W	-	–34	–28	dBc
ACPR	adjacent channel power ratio	$P_{L(AV)}$ = 25 W	-	–38	–33	dBc

7.1 Ruggedness in class-AB operation

The BLF6G20-110 and BLF6G20LS-110 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 900 mA; P_L = 110 W (CW); f = 1990 MHz.

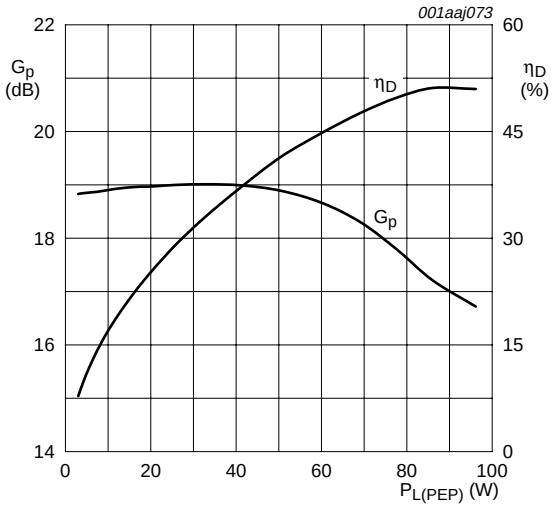
7.2 One-tone CW



V_{DS} = 30 V; I_{Dq} = 1400 mA; f = 1960 MHz.

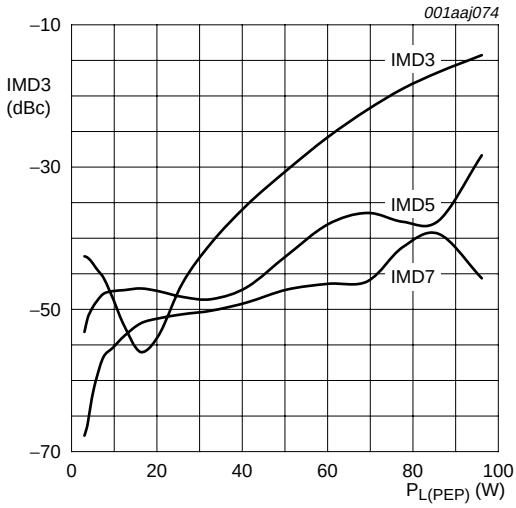
Fig 1. One-tone CW power gain and drain efficiency as function of load power; typical values

7.3 Two-tone CW



V_{DS} = 30 V; I_{Dq} = 1400 mA; f = 1960 MHz.

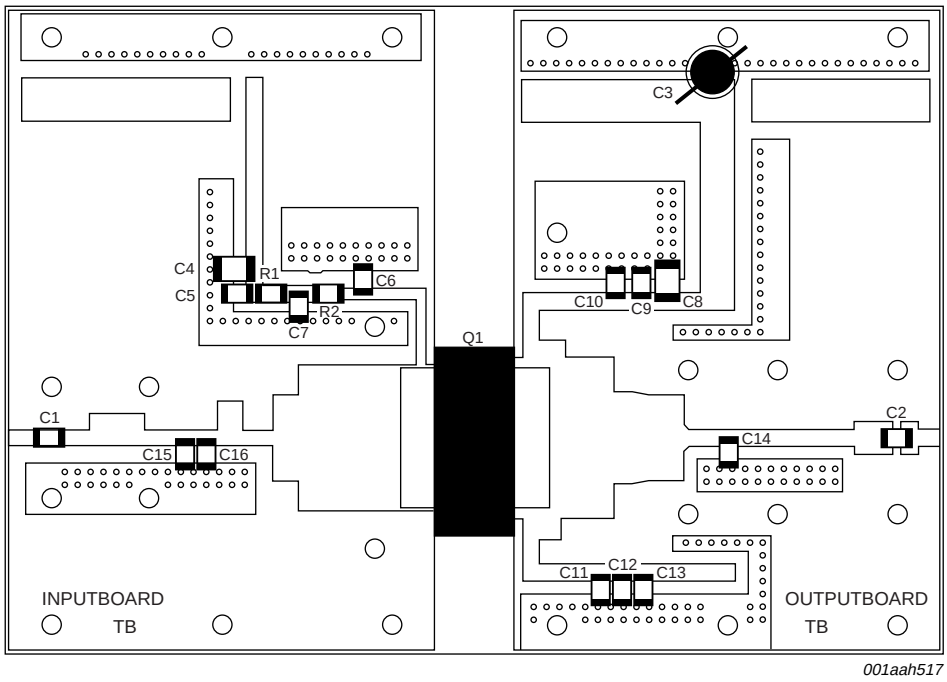
Fig 2. Two-tone CW power gain and drain efficiency as function of peak envelope load power; typical values



V_{DS} = 30 V; I_{Dq} = 1400 mA; f = 1960 MHz.

Fig 3. Two-tone CW intermodulation distortion as a function of peak envelope load power; typical values

8. Test information



The striplines are on a double copper-clad Taconic RF35 Printed-Circuit Board (PCB) with ε_r = 3.5 and thickness = 0.76 mm.

See Table 8 for list of components.

Fig 4. Component layout

Table 8. List of components (see Figure 4).

Component	Description	Value		Remarks
C1	multilayer ceramic chip capacitor	8.2 pF	[1]	
C2	multilayer ceramic chip capacitor	10 pF	[1]	
C3	electrolytic capacitor	100 µF; 63 V		
C4, C8	multilayer ceramic chip capacitor	4.7 µF; 25 V	[2]	
C5, C7, C12, C13	multilayer ceramic chip capacitor	220 nF; 50 V	[3]	
C6, C10, C11	multilayer ceramic chip capacitor	13 pF	[1]	
C9	multilayer ceramic chip capacitor	330 nF; 50 V	[3]	
C14	multilayer ceramic chip capacitor	1.0 pF	[1]	
C15	multilayer ceramic chip capacitor	1.5 pF	[1]	
C16	multilayer ceramic chip capacitor	0.6 pF	[1]	
Q1	BLF6G20-110 or BLF6G20LS-110	-		
R1	SMD resistor	1.0 Ω		
R2	SMD resistor	2.7 Ω		

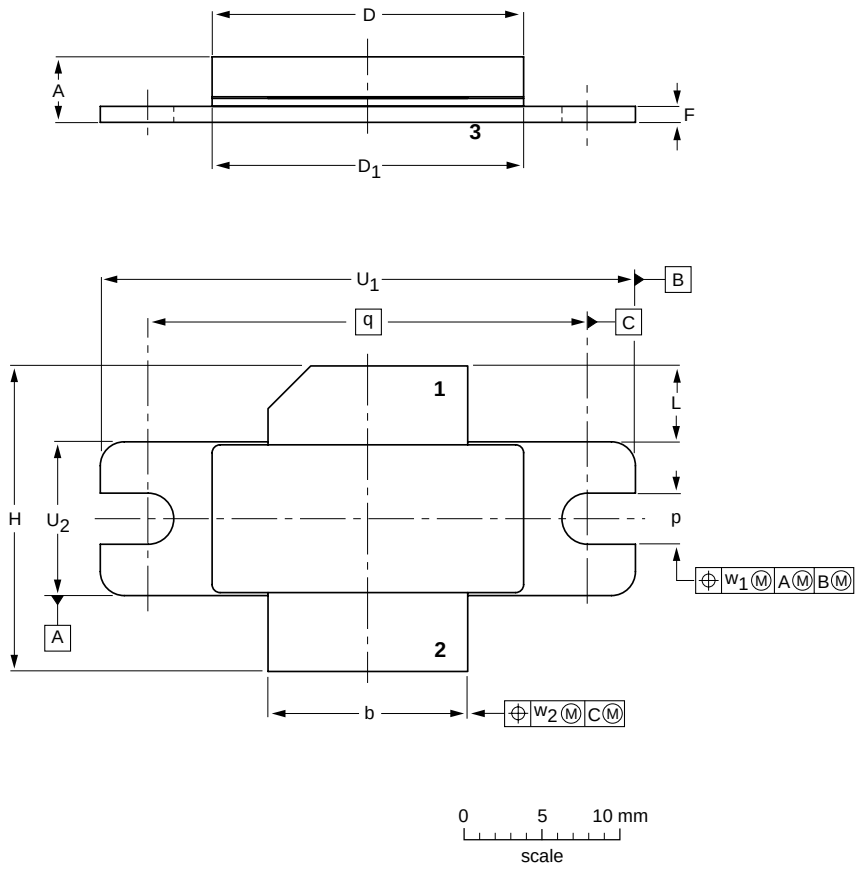
[1] American Technical Ceramics type 100B or capacitor of same quality.

[2] TDK or capacitor of same quality.

[3] AVX or capacitor of same quality.

9. Package outline

Flanged LDMOST ceramic package; 2 mounting holes; 2 leads **SOT502A**



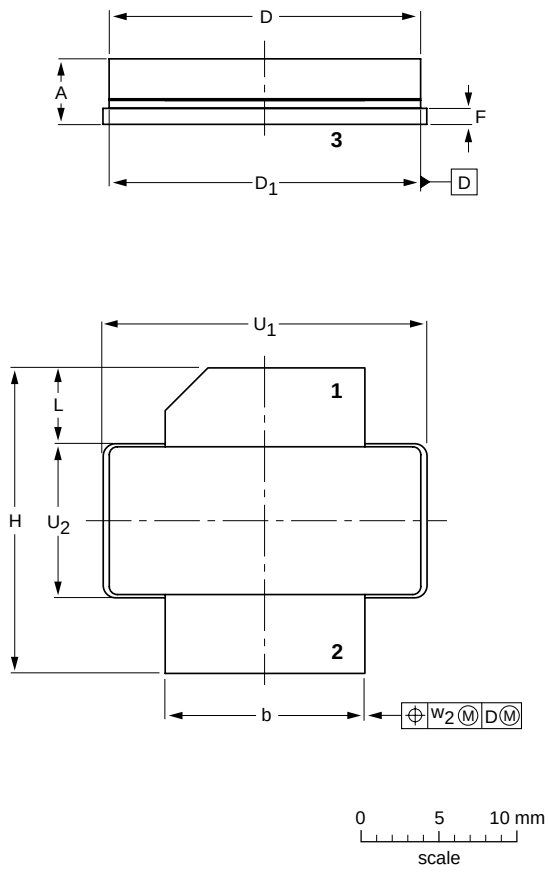
DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D_1	E	E_1	F	H	L	p	Q	q	U_1	U_2	w_1	w_2
mm	4.72 3.43	12.83 12.57	0.15 0.08	20.02 19.61	19.96 19.66	9.50 9.30	9.53 9.25	1.14 0.89	19.94 18.92	5.33 4.32	3.38 3.12	1.70 1.45	27.94	34.16 33.91	9.91 9.65	0.25	0.51
inches	0.186 0.135	0.505 0.495	0.006 0.003	0.788 0.772	0.786 0.774	0.374 0.366	0.375 0.364	0.045 0.035	0.785 0.745	0.210 0.170	0.133 0.123	0.067 0.057	1.100	1.345 1.335	0.390 0.380	0.01	0.02

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT502A						~~99-12-28~~ 03-01-10

Fig 5. Package outline SOT502A

Earless flanged LDMOST ceramic package; 2 leads **SOT502B**



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D_1	E	E_1	F	H	L	Q	U_1	U_2	w_2
mm	4.72 3.43	12.83 12.57	0.15 0.08	20.02 19.61	19.96 19.66	9.50 9.30	9.53 9.25	1.14 0.89	19.94 18.92	5.33 4.32	1.70 1.45	20.70 20.45	9.91 9.65	0.25
inches	0.186 0.135	0.505 0.495	0.006 0.003	0.788 0.772	0.786 0.774	0.374 0.366	0.375 0.364	0.045 0.035	0.785 0.745	0.210 0.170	0.067 0.057	0.815 0.805	0.390 0.380	0.010

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT502B						~~03-01-10~~ 07-05-09

Fig 6. Package outline SOT502B

10. Abbreviations

Table 9. Abbreviations

Acronym	Description
3GPP	Third Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CDMA	Code Division Multiple Access
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
EDGE	Enhanced Data rates for GSM Evolution
EVM	Error Vector Magnitude
GSM	Global System for Mobile communications
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
PAR	Peak-to-Average power Ratio
PDPCH	transmission Power of the Dedicated Physical CHannel
RF	Radio Frequency
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF6G20-110_BLF6G20LS-110_3	20090113	Product data sheet	-	BLF6G20-110_BLF6G20LS-110_2
Modifications:	• Figure 1 on page 4: Power gain curve corrected • Figure 2 on page 4: Power gain curve corrected			
BLF6G20-110_BLF6G20LS-110_2	20081117	Product data sheet	-	BLF6G20-110_BLF6G20LS-110_1
BLF6G20-110_BLF6G20LS-110_1	20080128	Preliminary data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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